

# B Sermage

## List of Publications by Year in descending order

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62  
papers

2,880  
citations

279798

23  
h-index

168389

53  
g-index

63  
all docs

63  
docs citations

63  
times ranked

2080  
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced Spontaneous Emission by Quantum Boxes in a Monolithic Optical Microcavity. Physical Review Letters, 1998, 81, 1110-1113.	7.8	946
2	Enhanced radiative recombination of free excitons in GaAs quantum wells. Physical Review Letters, 1991, 67, 2355-2358.	7.8	310
3	Enhanced radiative recombination of free excitons in GaAs quantum wells. Surface Science, 1992, 263, 491-495.	1.9	177
4	InAs quantum boxes: Highly efficient radiative traps for light emitting devices on Si. Applied Physics Letters, 1996, 68, 3123-3125.	3.3	155
5	Microcavity polariton spin quantum beats without a magnetic field: A manifestation of Coulomb exchange in dense and polarized polariton systems. Physical Review B, 2005, 72, .	3.2	116
6	Time-resolved spontaneous emission of excitons in a microcavity: Behavior of the individual exciton-photon mixed states. Physical Review B, 1996, 53, 16516-16523.	3.2	103
7	Microcavity polariton depopulation as evidence for stimulated scattering. Physical Review B, 2000, 62, R16263-R16266.	3.2	86
8	Photoexcited carrier lifetime and Auger recombination in 1.3 $\mu\text{m}$ InGaAsP. Applied Physics Letters, 1983, 42, 259-261.	3.3	82
9	Tunnelling and Relaxation in Coupled Quantum Wells. Europhysics Letters, 1990, 11, 367-372.	2.0	64
10	Comparison of Auger recombination in GaInAs-AlInAs multiple quantum well structure and in bulk GaInAs. IEEE Journal of Quantum Electronics, 1986, 22, 774-780.	1.9	62
11	Reabsorption of the excitonic luminescence in direct band gap semiconductors. Physical Review B, 1977, 15, 3935-3946.	3.2	58
12	Microfabrication and optical study of reactive ion etched InGaAsP/InP and GaAs/GaAlAs quantum wires. Applied Physics Letters, 1990, 56, 830-832.	3.3	57
13	Temperature dependence of carrier lifetime and Auger recombination in 1.3 $\mu\text{m}$ InGaAsP. Journal of Applied Physics, 1985, 57, 5443-5449.	2.5	52
14	Time-resolved probing of the Purcell effect for InAs quantum boxes in GaAs microdisks. Applied Physics Letters, 2001, 78, 2828-2830.	3.3	45
15	Time-resolved exciton transfer in GaAs/AlxGa1-xAs double-quantum-well structures. Physical Review B, 1992, 45, 11782-11794.	3.2	44
16	In-plane propagation of excitonic cavity polaritons. Physical Review B, 2000, 61, 7233-7236.	3.2	44
17	Annular resonant Rayleigh scattering in the picosecond dynamics of cavity polaritons. Physical Review B, 1999, 60, R8509-R8512.	3.2	37
18	Radiative and non-radiative recombination in GaAs/AlxGa1-xAs quantum wells. Superlattices and Microstructures, 1989, 6, 373-376.	3.1	35

#	ARTICLE	IF	CITATIONS
19	Dynamics of microcavity polaritons in the presence of an electron gas. <i>Physical Review B</i> , 2006, 73, .	3.2	31
20	Very high gain in carbon-doped base heterojunction bipolar transistor grown by chemical beam epitaxy. <i>Electronics Letters</i> , 1992, 28, 1344.	1.0	29
21	quantum boxes obtained by self-organized growth: Intrinsic electronic properties and applications. <i>Solid-State Electronics</i> , 1996, 40, 807-814.	1.4	29
22	Monitoring the dynamics of a coherent cavity polariton population. <i>Physical Review B</i> , 2005, 71, .	3.2	29
23	Electron and hole transport properties in GaAs-AlGaAs superlattices. <i>Journal of Luminescence</i> , 1989, 44, 277-283.	3.1	27
24	Density-dependent transition from electron to ambipolar vertical transport in short-period GaAs-AlGaAs superlattices. <i>Semiconductor Science and Technology</i> , 1989, 4, 513-517.	2.0	23
25	Radiative recombination lifetime of excitons in self-organized InAs/GaAs quantum dots. <i>Solid State Communications</i> , 2003, 128, 213-217.	1.9	23
26	Radiative recombination of free excitons in GaAs quantum wells. <i>Superlattices and Microstructures</i> , 1993, 13, 271.	3.1	20
27	Polariton acceleration in a microcavity wedge. <i>Physical Review B</i> , 2001, 64, .	3.2	18
28	Electrochemical capacitance voltage measurements in highly doped silicon and silicon-germanium alloys. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	18
29	Vertical transport of electrons and holes in short period GaAs $\delta$ -AlGaAs superlattices. <i>Superlattices and Microstructures</i> , 1989, 5, 565-567.	3.1	12
30	High static performance GaInAs-GaInAsP SCH MQW 1.5 $\mu$ m wavelength buried ridge stripe lasers. <i>IEEE Journal of Quantum Electronics</i> , 1991, 27, 1794-1797.	1.9	11
31	Cd <sub>0.88</sub> Zn <sub>0.12</sub> Te group index measurements near the exciton energy at low temperature. <i>Journal of Applied Physics</i> , 1998, 83, 7903-7908.	2.5	11
32	CBE growth of carbon doped InGaAs/InP HBTs for 25Gbit/s circuits. <i>Journal of Crystal Growth</i> , 1998, 188, 349-354.	1.5	10
33	Very Low Temperature (Cyclic) Deposition / Etch of In Situ Boron-Doped SiGe Raised Sources and Drains. <i>ECS Journal of Solid State Science and Technology</i> , 2014, 3, P382-P390.	1.8	10
34	Investigation of carbon-doped base materials grown by CBE for Al-free InP HBTs. <i>Journal of Crystal Growth</i> , 2000, 209, 476-480.	1.5	9
35	Thermal emission and band-filling effects on the photoluminescence rise time of InGaAs/InAs/GaAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 28, 22-27.	2.7	8
36	Very low temperature (450 $\hat{\text{A}}^{\circ}\text{C}$ ) selective epitaxial growth of heavily<i>in situ</i> boron-doped SiGe layers. <i>Semiconductor Science and Technology</i> , 2015, 30, 115006.	2.0	8

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37	Radiative and non-radiative recombination in GaAs <sub>1-x</sub> AlGaAs superlattices. Surface Science, 1990, 228, 210-212.	1.9	7
38	Luminescence of narrow RIE etched In <sub>1-x</sub> Ga <sub>x</sub> As/InP and GaAs/Ga <sub>1-x</sub> Al <sub>x</sub> As quantum wires. Surface Science, 1992, 267, 253-256.	1.9	7
39	Differentiation of the non radiative recombination properties of the two interfaces of MBE grown GaAs-GaAlAs quantum wells. Superlattices and Microstructures, 1990, 8, 417-419.	3.1	6
40	Quasi-planar GaAs heterojunction bipolar transistor device entirely grown by chemical beam epitaxy. Journal of Crystal Growth, 1994, 136, 235-240.	1.5	6
41	Time-Resolved Measurement of Stimulated Polariton Relaxation. Physica Status Solidi A, 2002, 190, 827-831.	1.7	6
42	Optical characterization of the interface in GaAs/AlAs quantum wells. Surface Science, 1992, 267, 199-203.	1.9	5
43	Improved stability of C-doped GaAs grown by chemical beam epitaxy for heterojunction bipolar transistor applications. Journal of Crystal Growth, 1996, 158, 210-216.	1.5	5
44	Improvement of CBE grown InGaAs/InP HBT's using a carbon doped and compositionally graded base. , 0, , .		5
45	Lifetime of excitons in GaAs quantum wells. European Physical Journal Special Topics, 1993, 03, 19-25.	0.2	5
46	Determination of the exciton energy from electron beam excited luminescence in direct gap semiconductors. Solid-State Electronics, 1978, 21, 1361-1363.	1.4	4
47	Time resolved stimulated emission in excitonic semiconductor microcavities. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 390-393.	2.7	4
48	INTERFACE RECOMBINATION IN GaAs-GaAlAs QUANTUM WELLS. Journal De Physique Colloque, 1987, 48, C5-135-C5-138.	0.2	4
49	Interpretation of the $1/C^{2/3}$ Curvature and Discontinuity in Electrochemical Capacitance Voltage Profiling of Heavily Ga Implanted SiGe Followed by Melt Laser Annealing. ECS Journal of Solid State Science and Technology, 2020, 9, 123008.	1.8	4
50	Carrier lifetime in carbon doped In <sub>0.53</sub> Ga <sub>0.47</sub> As. , 0, , .		3
51	Non-Linear Spin-Dependent Polariton Emission in Semiconductor Microcavities. Physica Status Solidi A, 2002, 190, 407-411.	1.7	3
52	Temperature dependence of electronic vertical transport in short period GaAs <sub>1-x</sub> AlGaAs superlattices. Surface Science, 1990, 228, 446-448.	1.9	2
53	Nonguiding semiconductor microcavity: Exciton-photon mode splitting and photoluminescence dynamics. Solid-State Electronics, 1996, 40, 487-491.	1.4	2
54	Resonant Rayleigh scattering mediated by 2D cavity polaritons. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 676-680.	2.7	2

#	ARTICLE	IF	CITATIONS
55	Auger recombination in GaInAs <sub>1-x</sub> AlInAs multiple quantum well structure. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1985, 134, 417-421.	0.9	1
56	Properties of GaAs <sub>1-x</sub> AlAs type I superlattices. Superlattices and Microstructures, 1990, 8, 255-258.	3.1	0
57	Drift and Diffusion of Exciton-Polaritons in a Graded Quantum Microcavity. Physica Status Solidi A, 2001, 183, 23-27.	1.7	0
58	Propagation and Scattering of Exciton-Polaritons in a Graded Semiconductor Microcavity. Physica Status Solidi A, 2002, 190, 339-343.	1.7	0
59	Ballistic transport of exciton-polaritons in a graded quantum microcavity. Springer Proceedings in Physics, 2001, , 665-666.	0.2	0
60	Comparison of Auger recombination in a GaInAs/AlInAs multiple quantum well structure and in bulk GaInAs. , 1985, , .		0
61	Free Exciton Radiative Recombination in GaAs Quantum Wells. , 1993, , 129-144.		0
62	Coherence Effects on the Exciton Radiative Recombination in Quantum Wells. NATO ASI Series Series B: Physics, 1994, , 267-272.	0.2	0